

TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}\text{C}$)

Collector current

I_{CM} : -0.6A

Collector-base voltage

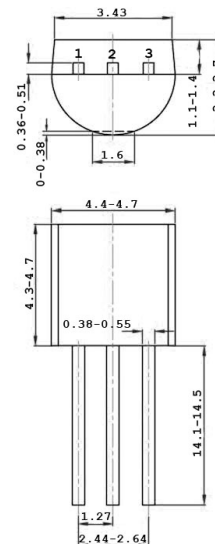
$V_{(BR)CBO}$: -160V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^{\circ}\text{C}$

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$		-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$		-0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	80		
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	80	250	
	$h_{FE(3)}$	$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-1	V
Transition frequency	f_r	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$ $f=30\text{MHz}$	100		MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	LH	MH	VH
Range	60-130	130-180	180-245